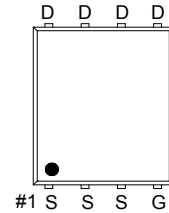
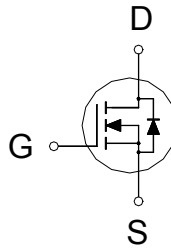




PRODUCT SUMMARY

$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D
80V	9m Ω	50A



G. GATE
D. DRAIN
S. SOURCE

ABSOLUTE MAXIMUM RATINGS ($T_A = 25\text{ }^{\circ}\text{C}$ Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNITS
Drain-Source Voltage		V_{DS}	80	V
Gate-Source Voltage		V_{GS}	± 20	V
Continuous Drain Current ³	$T_C = 25\text{ }^{\circ}\text{C}$	I_D	50	A
	$T_C = 100\text{ }^{\circ}\text{C}$		31	
Pulsed Drain Current ¹		I_{DM}	90	
Continuous Drain Current	$T_A = 25\text{ }^{\circ}\text{C}$	I_D	10	
	$T_A = 70\text{ }^{\circ}\text{C}$		8.7	
Avalanche Current		I_{AS}	49	
Avalanche Energy	$L = 0.1\text{mH}$	E_{AS}	120	mJ
Power Dissipation	$T_C = 25\text{ }^{\circ}\text{C}$	P_D	50	W
	$T_C = 100\text{ }^{\circ}\text{C}$		20	
Power Dissipation	$T_A = 25\text{ }^{\circ}\text{C}$	P_D	2.3	W
	$T_A = 70\text{ }^{\circ}\text{C}$		1.5	
Operating Junction & Storage Temperature Range		T_j, T_{stg}	-55 to 150	$^{\circ}\text{C}$

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Ambient ²	$R_{\theta JA}$		53	$^{\circ}\text{C} / \text{W}$
Junction-to-Case	$R_{\theta JC}$		2.5	

¹Pulse width limited by maximum junction temperature.

²The value of $R_{\theta JA}$ is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with $T_A = 25^{\circ}\text{C}$.

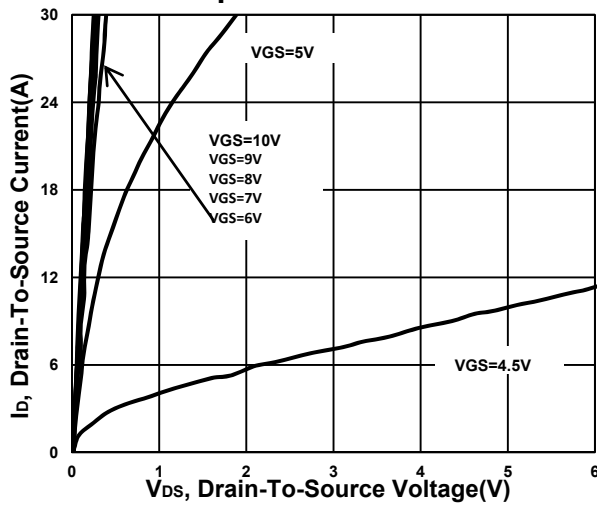
³Package limitation current is 50A.

ELECTRICAL CHARACTERISTICS ($T_J = 25\text{ }^{\circ}\text{C}$, Unless Otherwise Noted)

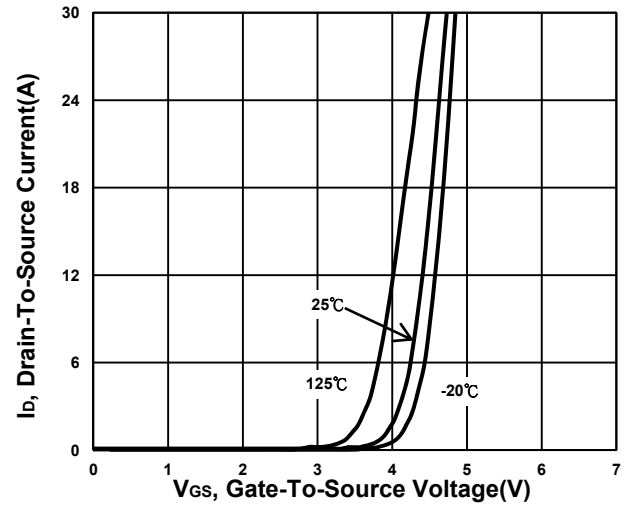
PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
STATIC						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	80			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	2	3	4	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0V, V_{GS} = \pm 20V$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 64V, V_{GS} = 0V$			1	μA
		$V_{DS} = 60V, V_{GS} = 0V, T_J = 55\text{ }^{\circ}C$			10	
Drain-Source On-State Resistance ¹	$R_{DS(ON)}$	$V_{GS} = 7V, I_D = 10A$		7.8	12	m Ω
		$V_{GS} = 10V, I_D = 10A$		7.2	9	
Forward Transconductance ¹	g_{fs}	$V_{DS} = 5V, I_D = 10A$		57		S
DYNAMIC						
Input Capacitance	C_{iss}	$V_{GS} = 0V, V_{DS} = 25V, f = 1MHz$		2824		pF
Output Capacitance	C_{oss}			322		
Reverse Transfer Capacitance	C_{rss}			178		
Gate Resistance	R_g	$V_{GS} = 0V, V_{DS} = 0V, f = 1MHz$		0.9		Ω
Total Gate Charge ²	Q_g	$V_{GS} = 10V$		53.2		nC
		$V_{GS} = 7V$		40.4		
Gate-Source Charge ²	Q_{gs}	$V_{DS} = 40V, V_{GS} = 10V, I_D = 10A$		13.5		
Gate-Drain Charge ²	Q_{gd}			17.8		
Turn-On Delay Time ²	$t_{d(on)}$	$V_{DS} = 40V, I_D \cong 10A, V_{GS} = 10V, R_{GEN} = 6\Omega$		35		nS
Rise Time ²	t_r			40		
Turn-Off Delay Time ²	$t_{d(off)}$			60		
Fall Time ²	t_f			40		
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS ($T_J = 25\text{ }^{\circ}C$)						
Continuous Current ³	I_S				38	A
Forward Voltage ¹	V_{SD}	$I_F = 10A, V_{GS} = 0V$			1.4	V
Reverse Recovery Time	t_{rr}	$I_F = 10A, di_F/dt = 100A / \mu S$		34		nS
Reverse Recovery Charge	Q_{rr}			37		nC

¹Pulse test : Pulse Width $\leq 300\text{ }\mu\text{sec}$, Duty Cycle $\leq 2\%$.²Independent of operating temperature.³Package limitation current is 50A.

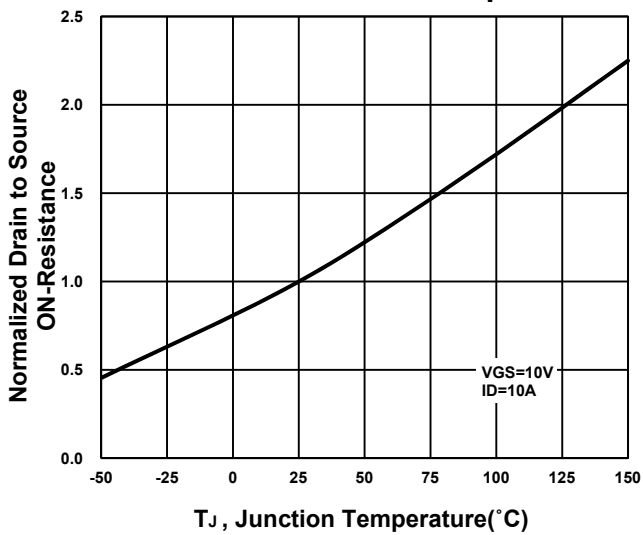
Output Characteristics



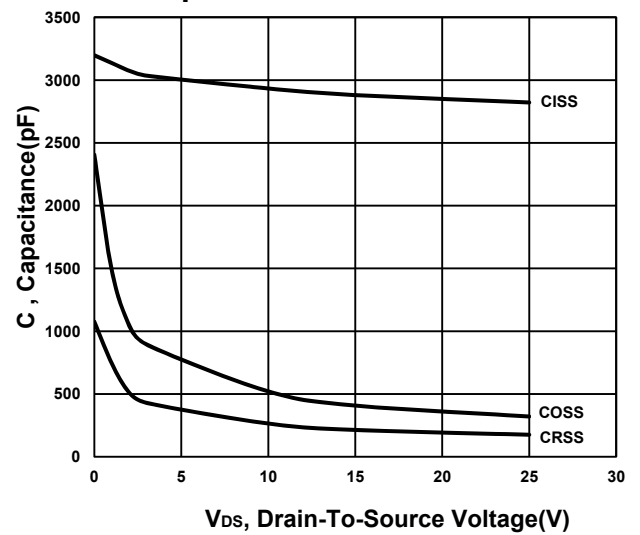
Transfer Characteristics



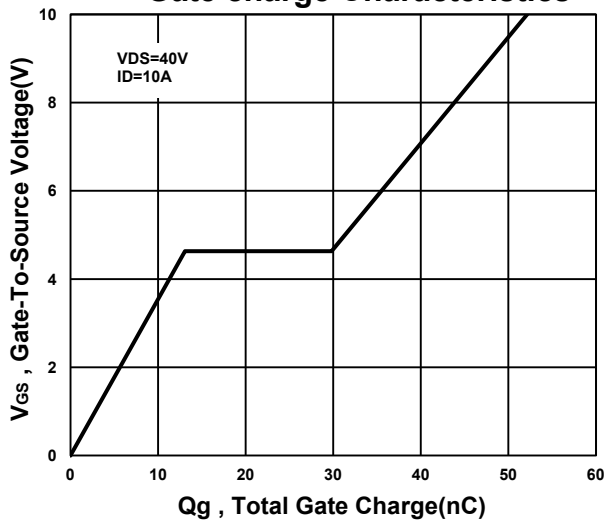
On-Resistance VS Temperature



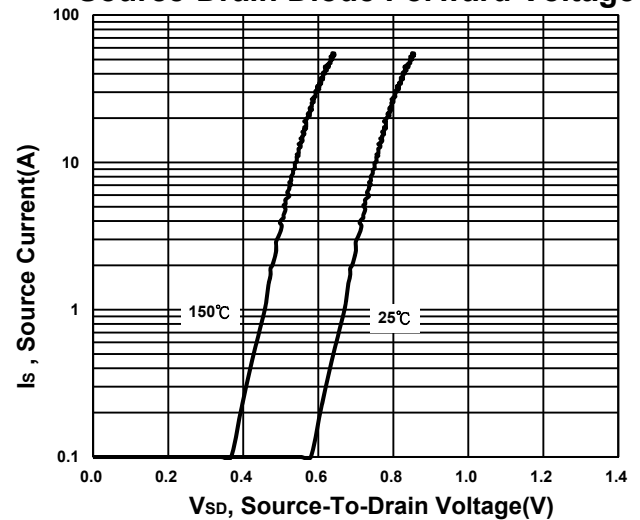
Capacitance Characteristic



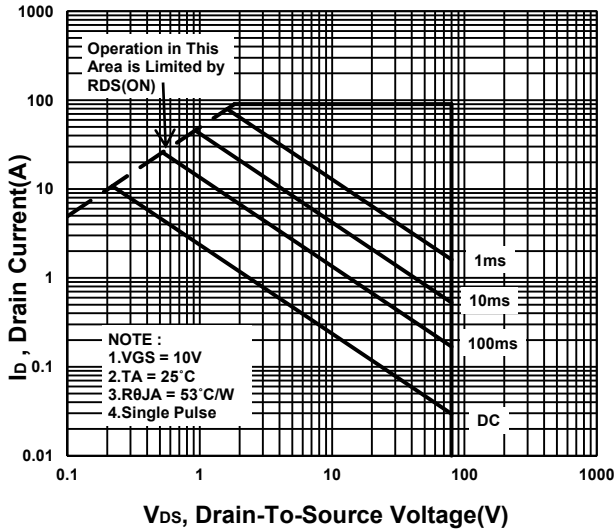
Gate charge Characteristics



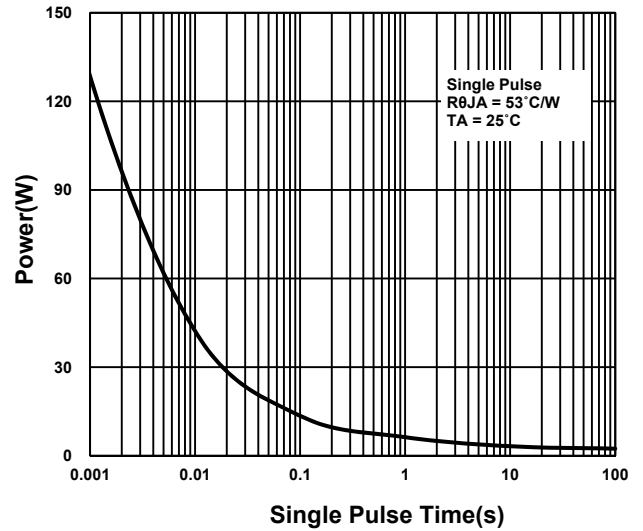
Source-Drain Diode Forward Voltage



Safe Operating Area



Single Pulse Maximum Power Dissipation



Transient Thermal Response Curve

